

Product Summary

BV_{DSS}	R_{D(S(ON))} Max	I_D Max T_A = +25°C
100V	52mΩ @ V _{GS} = 10V	5A
	75mΩ @ V _{GS} = 4.5V	4.1A

Description

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

Applications

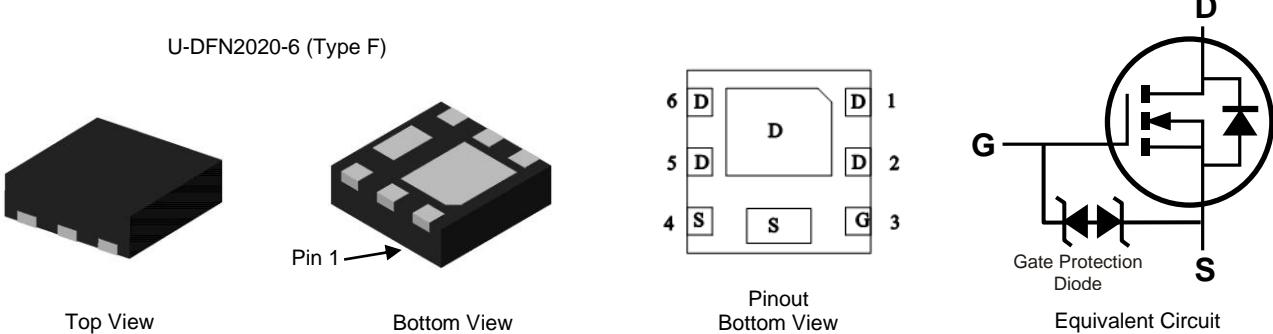
- Power-management functions
- Battery-operated systems and solid-state relays
- Drivers: relays, solenoids, lamps, hammers, displays, memories, transistors, etc.

Features and Benefits

- 0.6mm Profile – Ideal for Low Profile Applications
- PCB Footprint of 4mm²
- Low On-Resistance
- 100% Unclamped Inductive Switching (UIS) Test in Production – Ensures More Reliable and Robust End Application
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. “Green” Device (Note 3)**
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at
<https://www.diodes.com/products/automotive/automotive-products/>.
- This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.
<https://www.diodes.com/quality/product-definitions/>

Mechanical Data

- Package: U-DFN2020-6
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (4)
- Weight: 0.0065 grams (Approximate)



Ordering Information (Note 4)

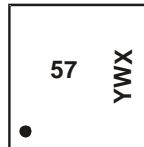
Orderable Part Number	Package	Packing	
		Qty.	Carrier
DMT10H052LFDF-7	U-DFN2020-6 (Type F)	3,000	Reel
DMT10H052LFDF-13	U-DFN2020-6 (Type F)	10,000	Reel

Notes:

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information

U-DFN2020-6 (Type F)



57 = Product Type Marking Code
 YWX = Date Code Marking
 Y or Y = Year (ex: 5 = 2025)
 W = Week (ex: a = week 27; z represents week 52 and 53)
 X = Internal Code (ex: U = Monday)

Date Code Key

Year	2019	-	2025	2026	2027	2028	2029	2030	2031	2032	2033	2034
Code	9	-	5	6	7	8	9	0	1	2	3	4
Week	1-26				27-52				53			
Code	A-Z				a-z				z			
Internal Code	Sun	Mon	Tue	Wed	Thu	Fri	Sat					
Code	T	U	V	W	X	Y	Z					

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	100	V
Gate-Source Voltage	V_{GSS}	± 20	V
Continuous Drain Current, $V_{GS} = 10\text{V}$ (Note 5)	I_D	5 4	A
Pulsed Drain Current (10 μs Pulse, Duty Cycle = 1%)	I_{DM}	30	A
Maximum Body Diode Continuous Current	I_S	2.3	A
Pulsed Body Diode Continuous Current (10 μs Pulse, Duty Cycle = 1%)	I_{SM}	30	A
Avalanche Current, $L = 0.1\text{mH}$ (Note 6)	I_{AS}	15.6	A
Avalanche Energy, $L = 0.1\text{mH}$ (Note 6)	E_{AS}	12.2	mJ

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 7)	P_D	0.8	W
$T_A = +70^\circ\text{C}$		0.5	
Thermal Resistance, Junction to Ambient (Note 7)	$R_{\theta JA}$	151	$^\circ\text{C/W}$
Total Power Dissipation (Note 5)	P_D	1.9	W
$T_A = +25^\circ\text{C}$		1.2	
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	64	$^\circ\text{C/W}$
Thermal Resistance, Junction to Case (Note 5)	$R_{\theta JC}$	11	
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Notes:

- 5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
- 6. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep $T_J = +25^\circ\text{C}$.
- 7. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	100	—	—	V	$\text{V}_{\text{GS}} = 0\text{V}$, $\text{I}_D = 1\text{mA}$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	μA	$\text{V}_{\text{DS}} = 80\text{V}$, $\text{V}_{\text{GS}} = 0\text{V}$
Gate-Source Leakage	I_{GSS}	—	—	± 10	μA	$\text{V}_{\text{GS}} = \pm 20\text{V}$, $\text{V}_{\text{DS}} = 0\text{V}$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$\text{V}_{\text{GS(TH)}}$	1.5	—	3.0	V	$\text{V}_{\text{DS}} = \text{V}_{\text{GS}}$, $\text{I}_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$\text{R}_{\text{DS(ON)}}$	—	38	52	$\text{m}\Omega$	$\text{V}_{\text{GS}} = 10\text{V}$, $\text{I}_D = 4\text{A}$
		—	54	75		$\text{V}_{\text{GS}} = 4.5\text{V}$, $\text{I}_D = 3\text{A}$
Diode Forward Voltage	V_{SD}	—	0.8	1.0	V	$\text{V}_{\text{GS}} = 0\text{V}$, $\text{I}_S = 1\text{A}$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	—	258	—	pF	$\text{V}_{\text{DS}} = 50\text{V}$, $\text{V}_{\text{GS}} = 0\text{V}$ $f = 1\text{MHz}$
Output Capacitance	C_{oss}	—	114	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	5.5	—	pF	
Gate Resistance	R_g	—	6.3	—	Ω	$\text{V}_{\text{DS}} = 0\text{V}$, $\text{V}_{\text{GS}} = 0\text{V}$, $f = 1\text{MHz}$
Total Gate Charge ($\text{V}_{\text{GS}} = 4.5\text{V}$)	Q_g	—	2.9	—	nC	$\text{V}_{\text{DS}} = 50\text{V}$, $\text{I}_D = 4\text{A}$
Total Gate Charge ($\text{V}_{\text{GS}} = 10\text{V}$)	Q_g	—	5.4	—	nC	
Gate-Source Charge	Q_{gs}	—	0.8	—	nC	
Gate-Drain Charge	Q_{gd}	—	1.6	—	nC	
Turn-On Delay Time	$\text{t}_{\text{D(ON)}}$	—	3.1	—	ns	$\text{V}_{\text{DS}} = 50\text{V}$, $\text{R}_L = 11\Omega$ $\text{V}_{\text{GS}} = 10\text{V}$, $\text{R}_{\text{GEN}} = 3\Omega$
Turn-On Rise Time	t_R	—	3.8	—	ns	
Turn-Off Delay Time	$\text{t}_{\text{D(OFF)}}$	—	11.4	—	ns	
Turn-Off Fall Time	t_F	—	4.4	—	ns	
Reverse-Recovery Time	t_{RR}	—	22.6	—	ns	$\text{I}_F = 4\text{A}$, $\text{dI}/\text{dt} = 300\text{A}/\mu\text{s}$
Reverse-Recovery Charge	Q_{RR}	—	43.6	—	nC	

Notes: 8. Short duration pulse test used to minimize self-heating effect.

9. Guaranteed by design. Not subject to product testing.

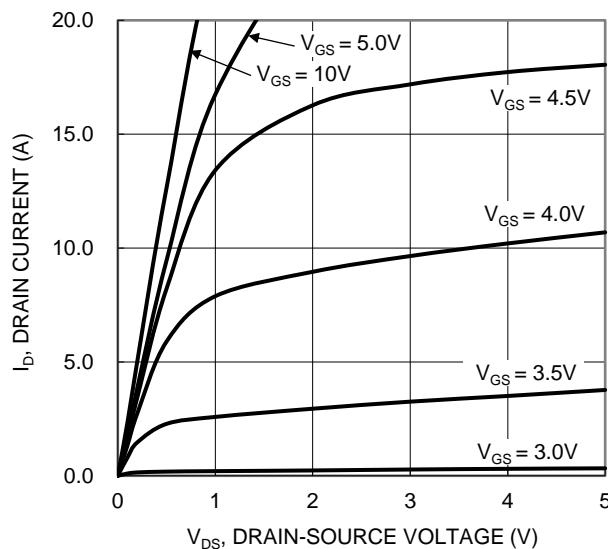


Figure 1. Typical Output Characteristic

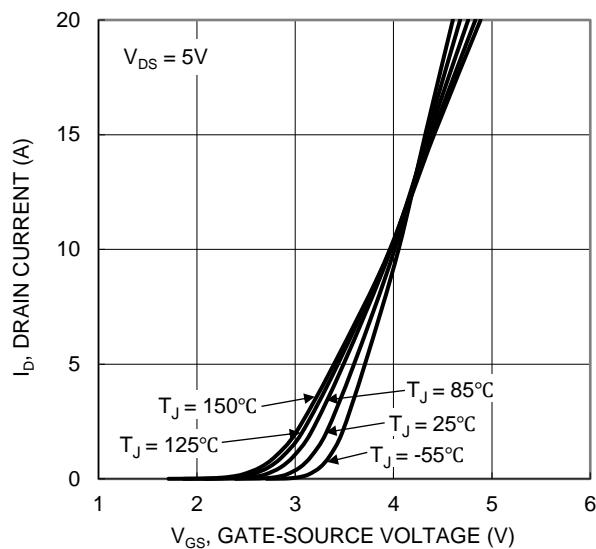


Figure 2. Typical Transfer Characteristic

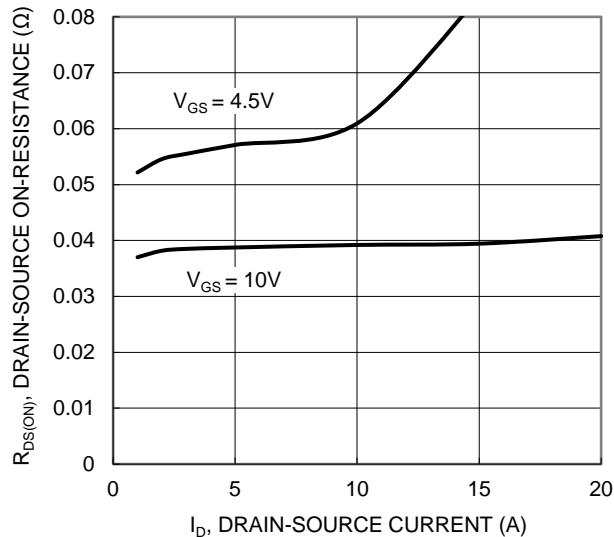


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

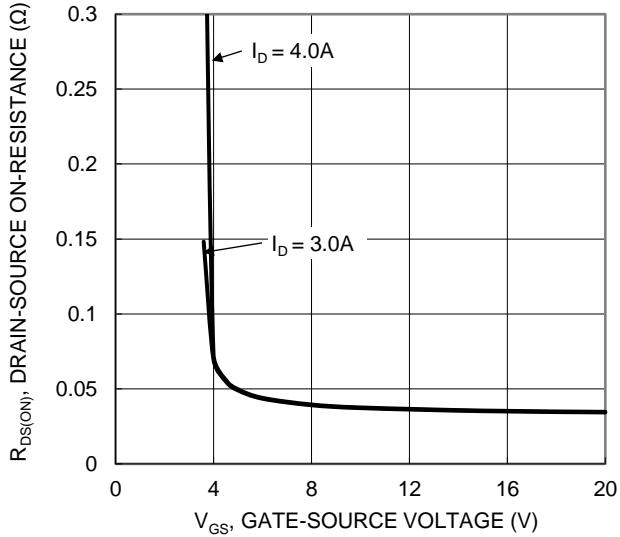


Figure 4. Typical Transfer Characteristic

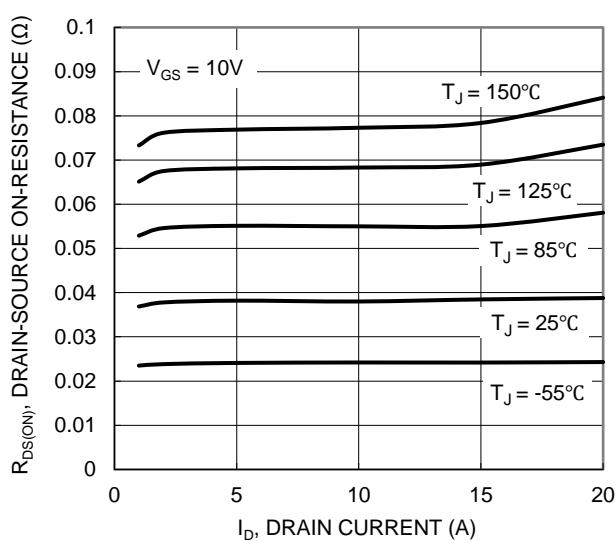


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

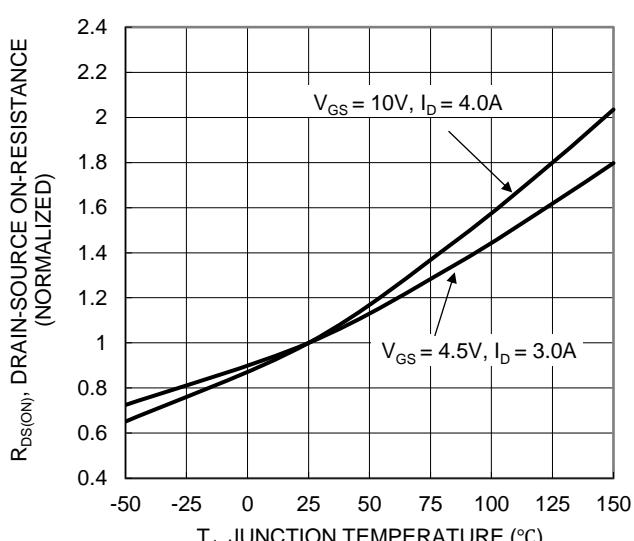


Figure 6. On-Resistance Variation with Junction Temperature

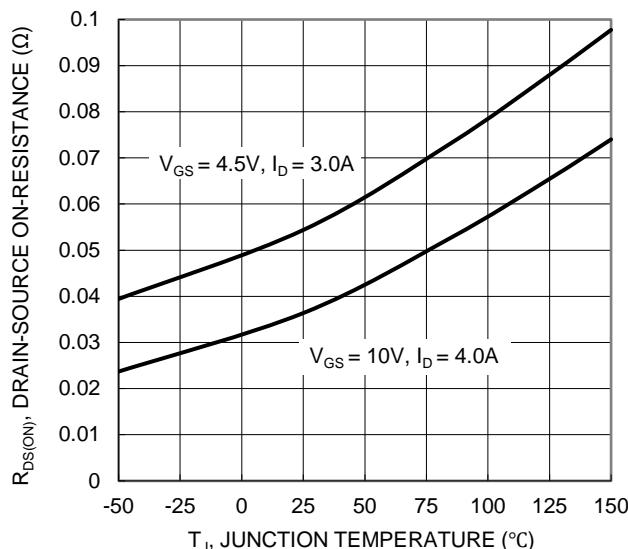


Figure 7. On-Resistance Variation with Junction Temperature

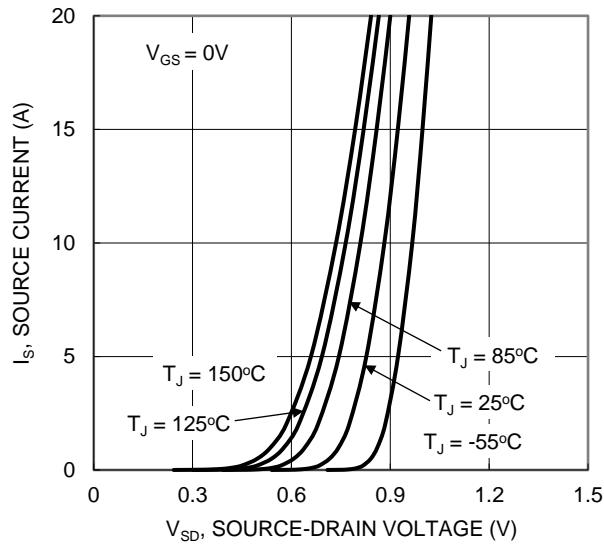


Figure 9. Diode Forward Voltage vs. Current

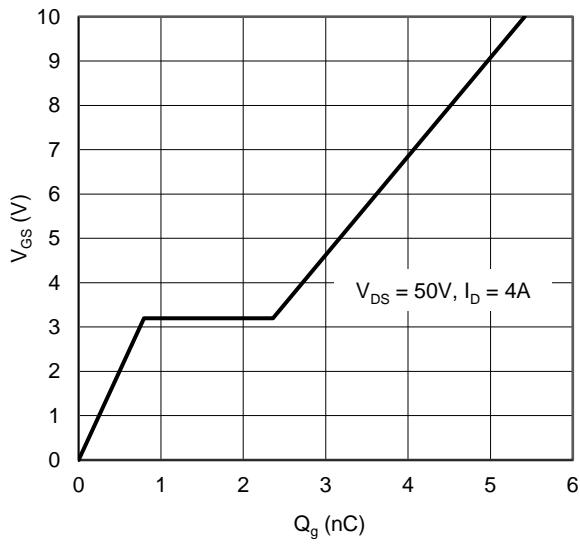


Figure 11. Gate Charge

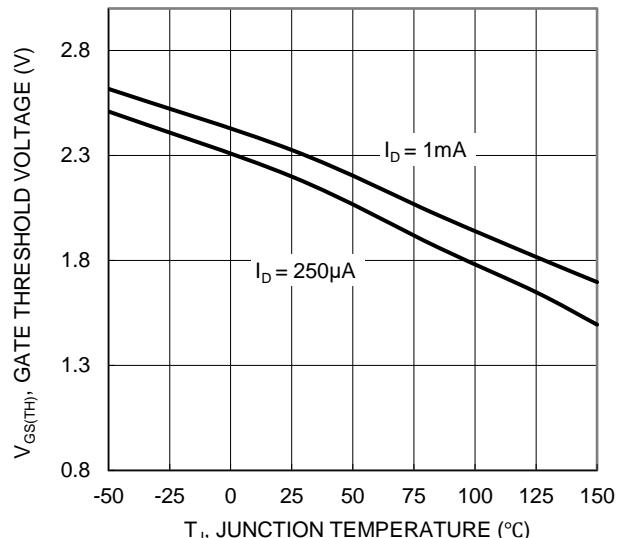


Figure 8. Gate Threshold Variation vs. Junction Temperature

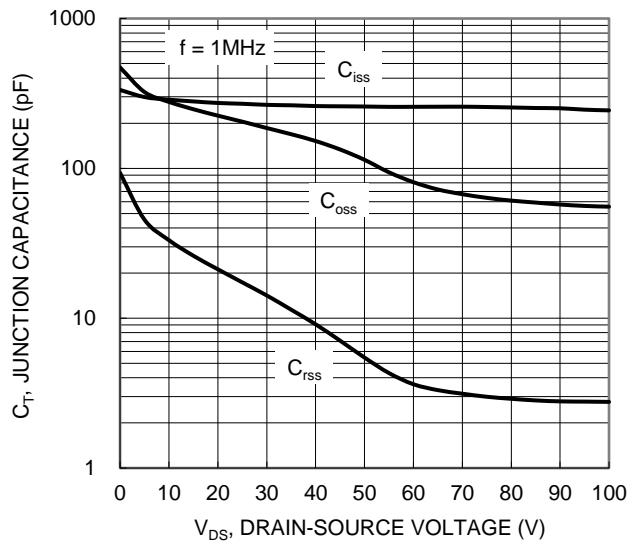


Figure 10. Typical Junction Capacitance

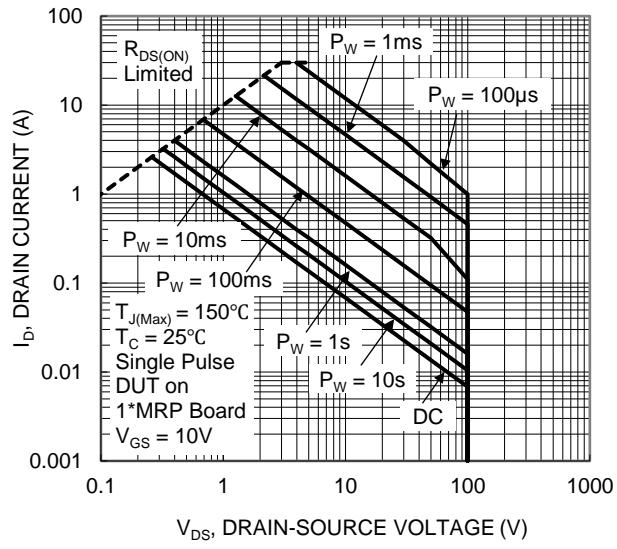


Figure 12. SOA, Safe Operation Area

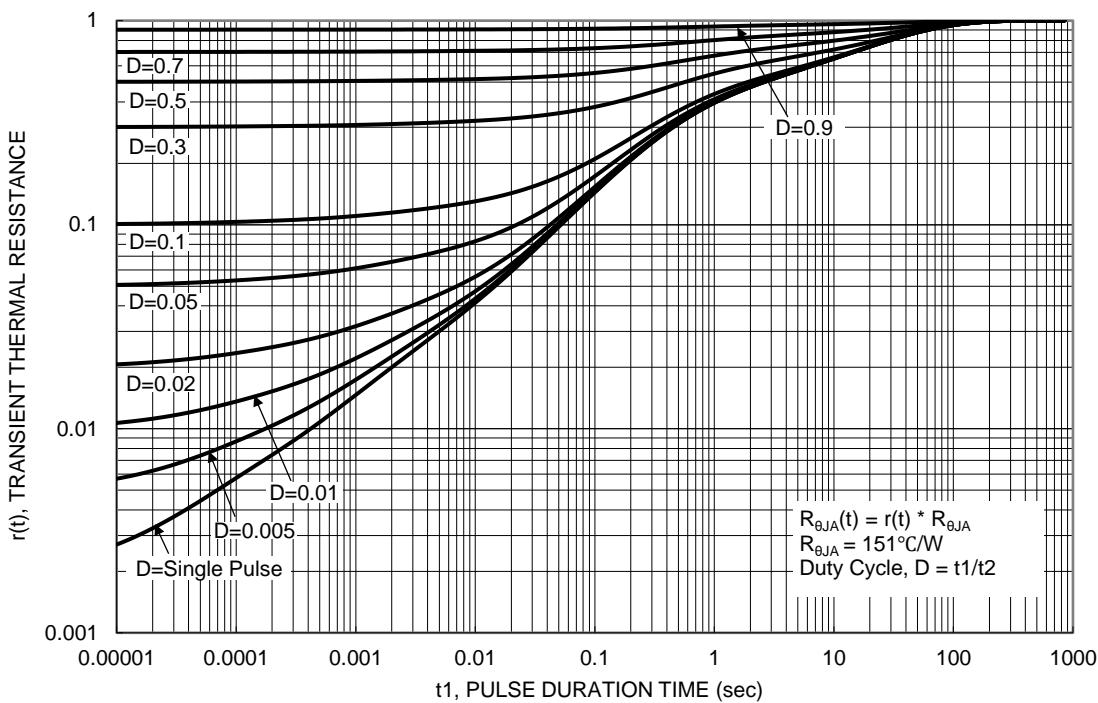
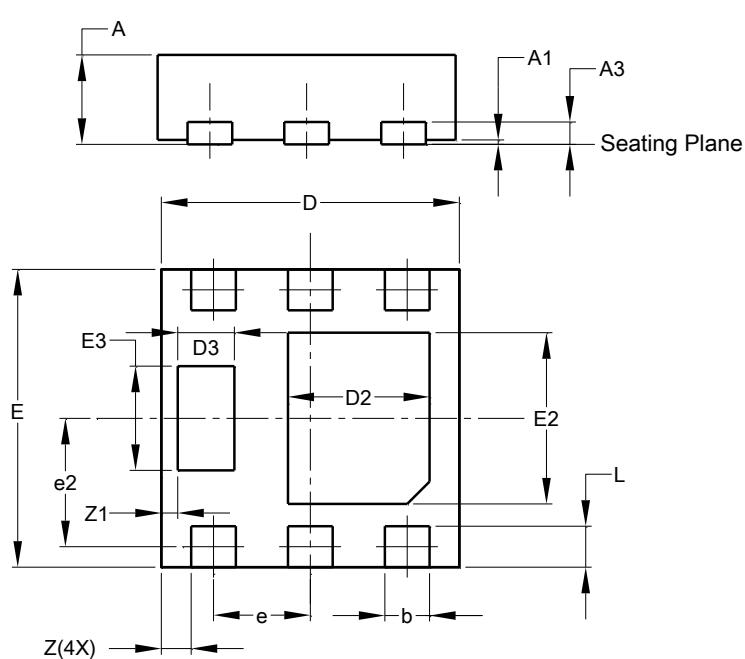


Figure 13. Transient Thermal Resistance

Package Outline Dimension

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

U-DFN2020-6 (Type F)

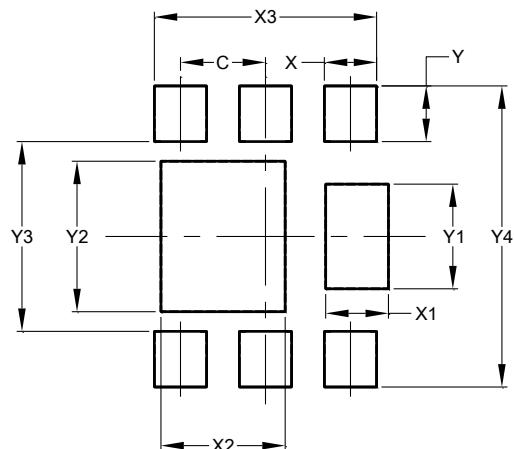


U-DFN2020-6 (Type F)			
Dim	Min	Max	Typ
A	0.57	0.63	0.60
A1	0.00	0.05	0.03
A3	-	-	0.15
b	0.25	0.35	0.30
D	1.95	2.05	2.00
D2	0.85	1.05	0.95
D2a	0.33	0.43	0.38
E	1.95	2.05	2.00
E2	1.05	1.25	1.15
E2a	0.65	0.75	0.70
e	0.65	BSC	
e2	0.863	BSC	
e3	0.70	BSC	
e4	0.325	BSC	
k	0.37	BSC	
k1	0.15	BSC	
k2	0.36	BSC	
L	0.225	0.325	0.275
z	0.20	BSC	
z1	0.110	BSC	
z2	0.20	BSC	
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

U-DFN2020-6 (Type F)



Dimensions	Value (in mm)
C	0.650
X	0.400
X1	0.480
X2	0.950
X3	1.700
Y	0.425
Y1	0.800
Y2	1.150
Y3	1.450
Y4	2.300

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